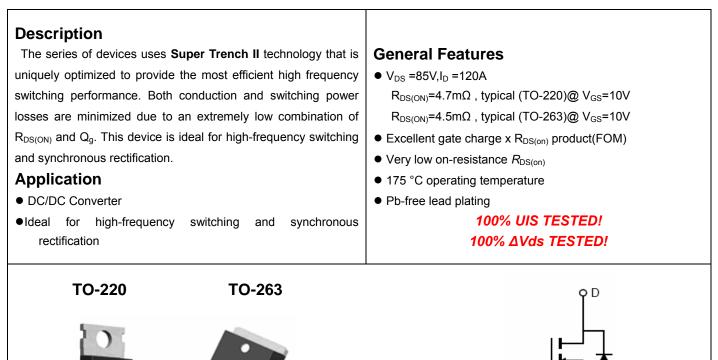


NCE N-Channel Super Trench II Power MOSFET



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP050N85	NCEP050N85	TO-220	-	-	-
NCEP050N85D	NCEP050N85D	TO-263	-	-	-

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	85	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	ID	120	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	88	А
Pulsed Drain Current	I _{DM}	480	А
Maximum Power Dissipation	PD	160	W
Derating factor		1.07	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	650	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

G

Schematic Diagram



NCEP050N85, NCEP050N85D

0.94

R_{ejc}

Thermal Characteristic

Thermal Resistance, Junction-to-Case^(Note 2)

°C/W

Electrical Characteristics (T_C=25 $^{\circ}$ C unless otherwise noted)

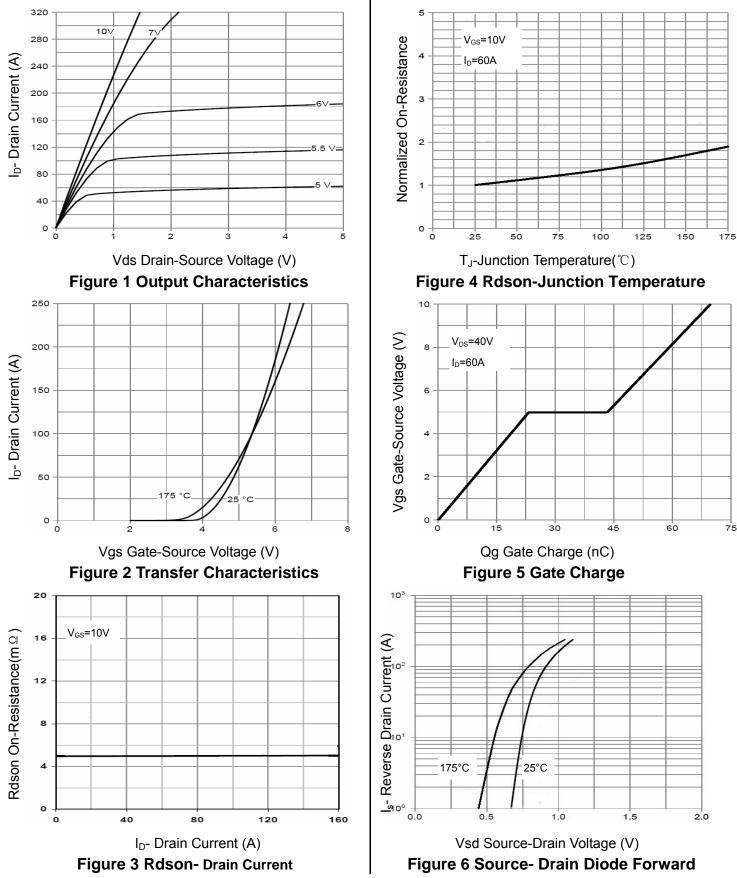
Parameter	Symbol	Condition		Min	Тур	Мах	Unit
Off Characteristics							•
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA		85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS} =0V		-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V		-	-	±100	nA
On Characteristics (Note 3)				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$		2.0	3.0	4.0	V
Desir Osumo On Otata Desistance	5	V _{GS} =10V, I _D =60A	TO-220	-	4.7	5.0	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}		TO-263		4.5	5.0	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =60A			60	-	S
Dynamic Characteristics (Note4)				•			
Input Capacitance	C _{lss}	- V _{DS} =40V,V _{GS} =0V, F=1.0MHz		-	3900	-	PF
Output Capacitance	Coss			-	650	-	PF
Reverse Transfer Capacitance	C _{rss}			-	27	-	PF
Switching Characteristics (Note 4)				•			
Turn-on Delay Time	t _{d(on)}			-	20	-	nS
Turn-on Rise Time	tr	V _{DD} =40V,I _D =60A V _{GS} =10V,R _G =1.6Ω		-	59	-	nS
Turn-Off Delay Time	t _{d(off)}			-	39	-	nS
Turn-Off Fall Time	t _f			-	11	-	nS
Total Gate Charge	Qg	- V _{DS} =40V,I _D =60A, - V _{GS} =10V		-	70	-	nC
Gate-Source Charge	Q _{gs}			-	23		nC
Gate-Drain Charge	Q _{gd}			-	20		nC
Drain-Source Diode Characteristics	1					. <u> </u>	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =60A		-		1.2	V
Diode Forward Current (Note 2)	ls			-	-	120	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F	= = I _S	-	66	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)		-	135	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^\circ \! \mathrm{C}$,V_DD=40V,V_G=10V,L=0.5mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics





NCEP050N85, NCEP050N85D

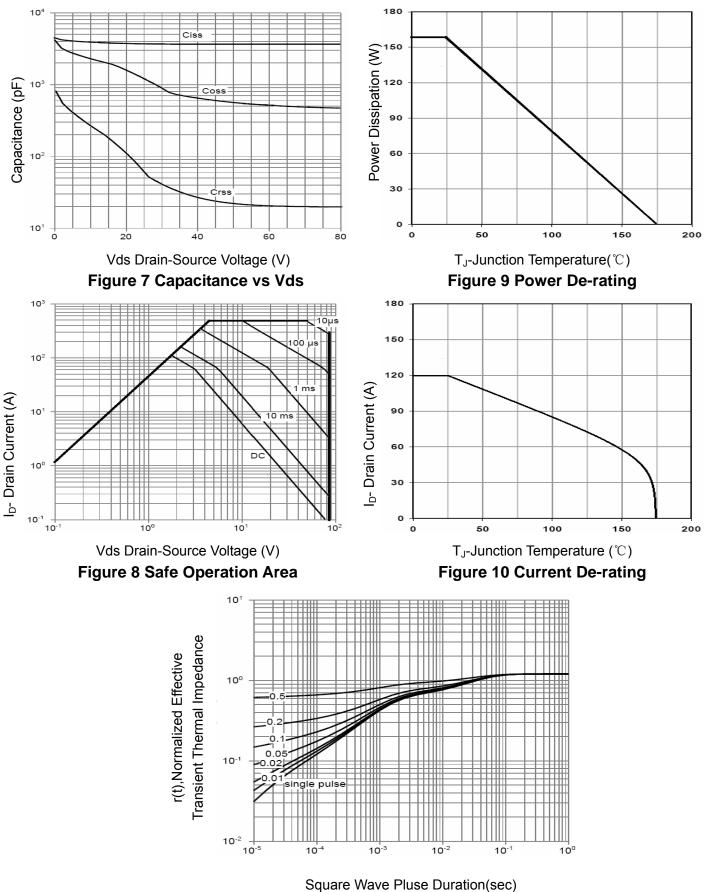
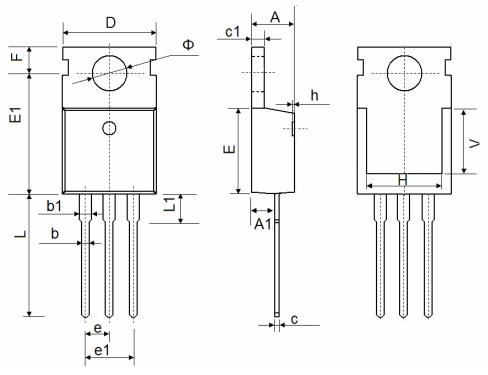


Figure 11 Normalized Maximum Transient Thermal Impedance



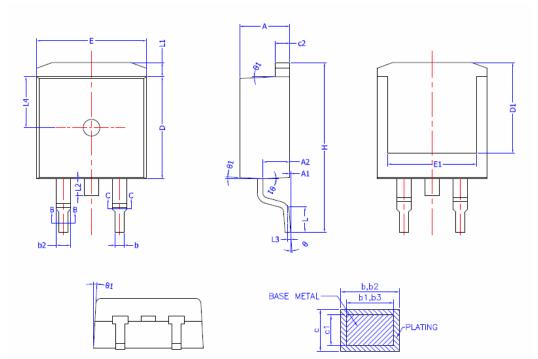
TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900 REF.		0.276 REF.		
Φ	3.400	3.800	0.134	0.150	



TO-263-2L Package Information



COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SECTION B-B&C-C

(UNITS OF MEASURE -MILLINETER)						
MIN	NOM	MAX				
4.40	4.50	4.60				
0	0.10	0.25				
2,20	2,40	2,60				
0,76		0,89				
0,75	0,80	0,85				
1,23		1,37				
1,22	1,27	1,32				
0,47		0,60				
0.46	0,51	0.56				
1,25	1,30	1.35				
9,10	9,20	9.30				
8.00		—				
9.80	9,90	10.00				
7.80	—	—				
2.54 BSC						
14,90	15,30	15.70				
2.00	2,30	2.60				
1.17	1.27	1.40				
		1,75				
0.25BSC						
4.60 REF						
		8°				
1°	3°	5°				
	MIN 4.40 0 2.20 0.76 0.75 1.23 1.22 0.47 0.46 1.25 9.10 8.00 9.80 7.80 2.1 14.90 2.00 1.17 — 0.2	MIN NOM 4.40 4.50 0 0.10 2.20 2.40 0.76 — 0.75 0.80 1.23 — 1.22 1.27 0.47 — 0.46 0.51 1.25 1.30 9.10 9.20 8.00 — 9.80 9.90 7.80 — 2.54 BSC 14.90 15.30 2.00 2.30 1.17 1.27 — — 0.25BSC 4.60 9.° —				



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